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**Ohno**

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(54) **SILICON CARBIDE SEMICONDUCTOR  
DEVICE AND METHOD FOR  
MANUFACTURING THE SAME**

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**H01L 23/482** (2006.01)

**H01L 21/04** (2006.01)

**H01L 29/45** (2006.01)

**H01L 29/66** (2006.01)

**H01L 29/872** (2006.01)

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21/3065** (2013.01); **H01L 23/4827** (2013.01);  
**H01L 29/45** (2013.01); **H01L 29/6606**  
(2013.01); **H01L 29/66143** (2013.01); **H01L  
29/872** (2013.01); **H01L 29/1608** (2013.01);  
**H01L 29/8611** (2013.01); **H01L 2924/0002**  
(2013.01)

(58) **Field of Classification Search**

IPC ..... **H01L 2924/0002, 2924/00**  
See application file for complete search history.

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*Primary Examiner* — Latanya N Crawford

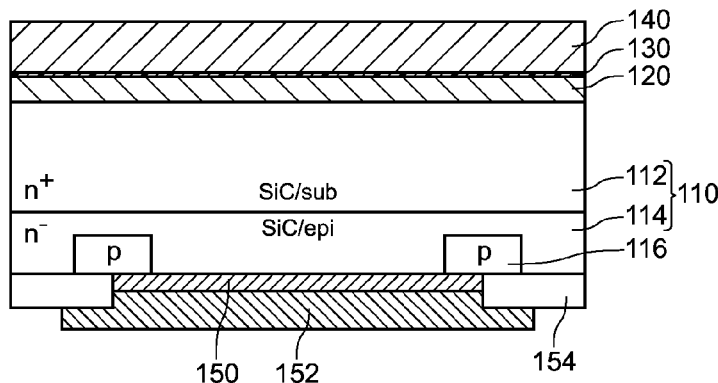
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(57) **ABSTRACT**

A silicon carbide semiconductor device includes: a silicon  
carbide layer, a reaction layer which is in contact with the  
silicon carbide layer, a conductive oxidation layer which is in  
contact with the reaction layer, and an electrode layer which  
is formed over the reaction layer with the conductive oxida-  
tion layer interposed therebetween. A thickness of the con-  
ductive oxidation layer falls within a range of 0.3 nm to 2.25  
nm.

**15 Claims, 9 Drawing Sheets**

100



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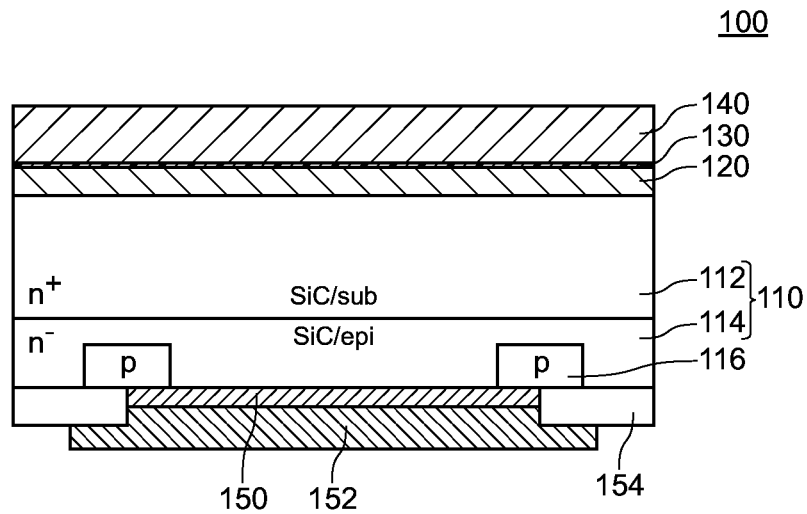


FIG.1

FIG. 2A

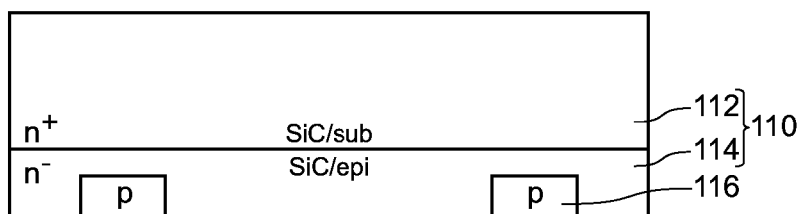


FIG. 2B

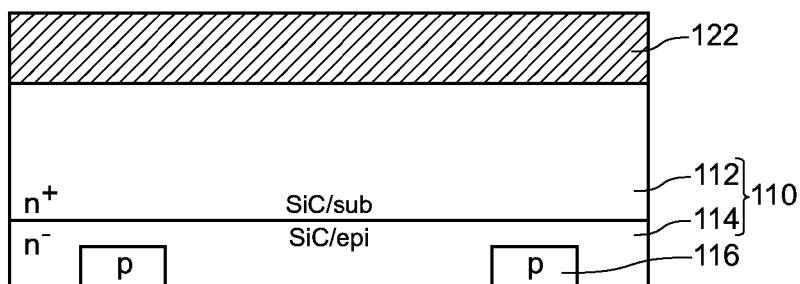


FIG. 2C

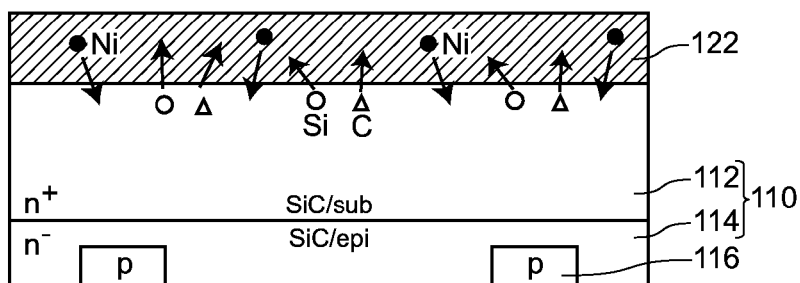


FIG. 2D

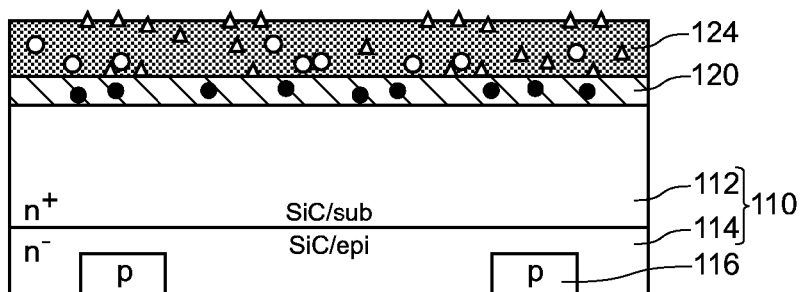


FIG. 2E

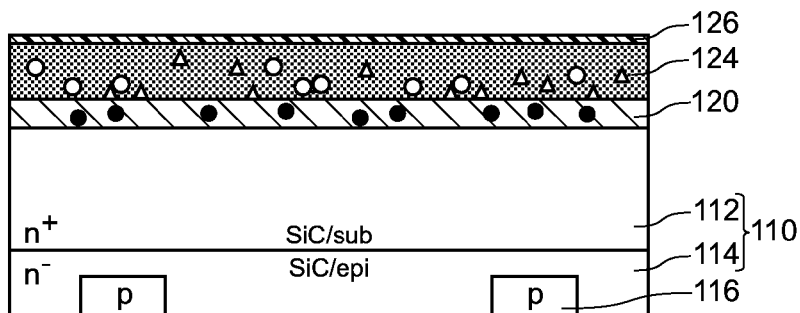


FIG.3A

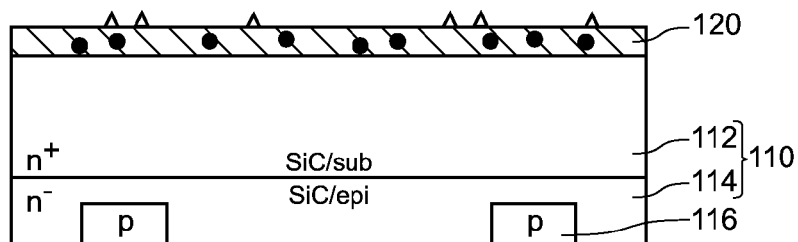


FIG.3B

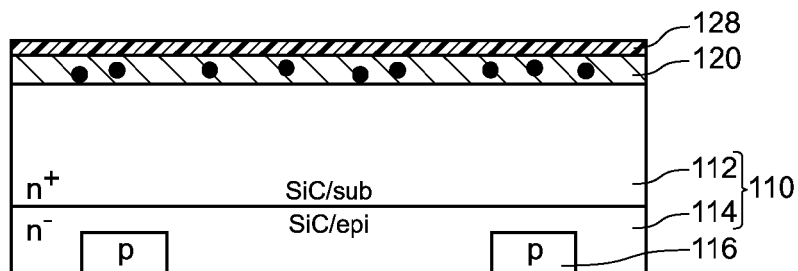


FIG.3C

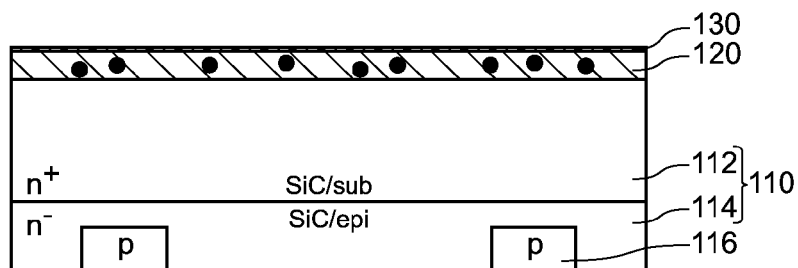


FIG.3D

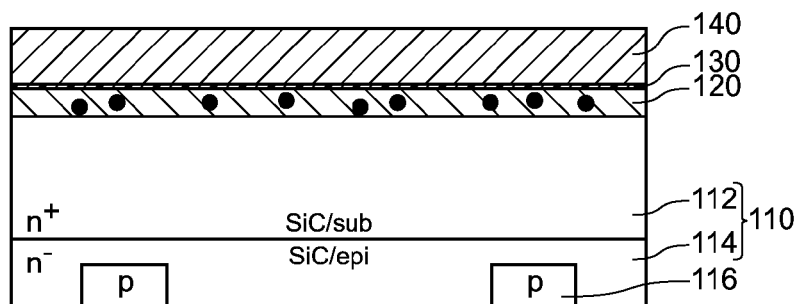
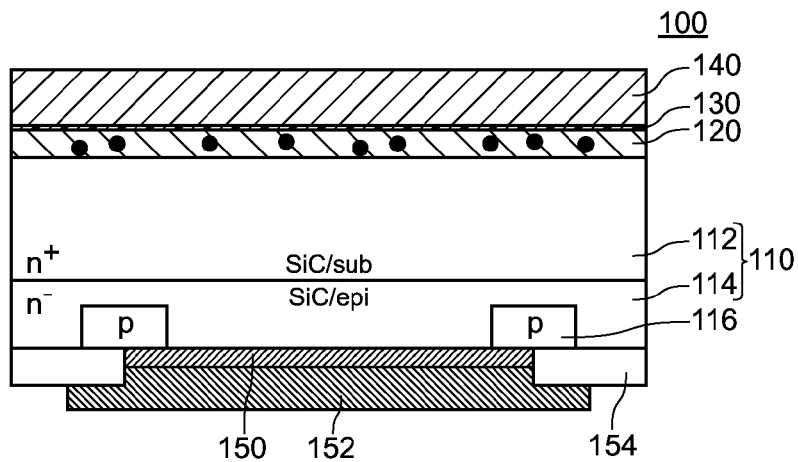
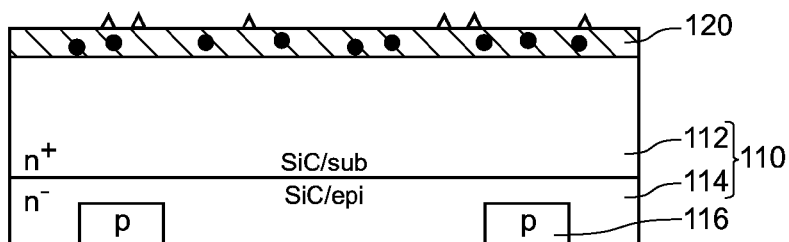


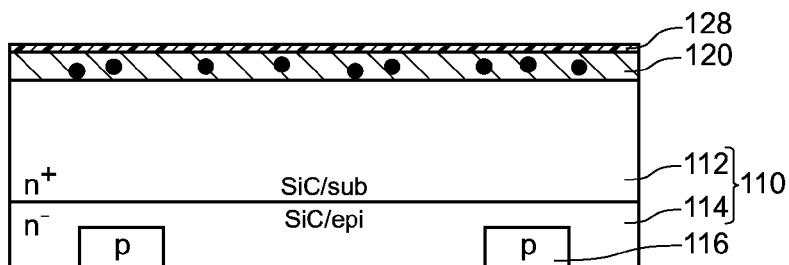
FIG.3E



**FIG.4A**



**FIG.4B**



**FIG.4C**

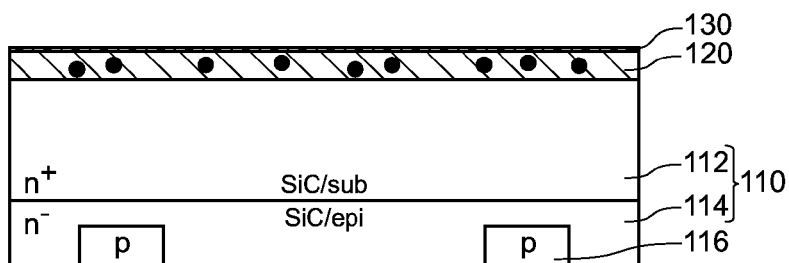
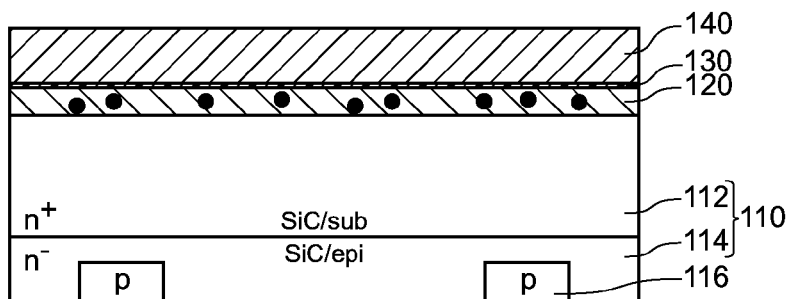


FIG.4D



**FIG.4E**

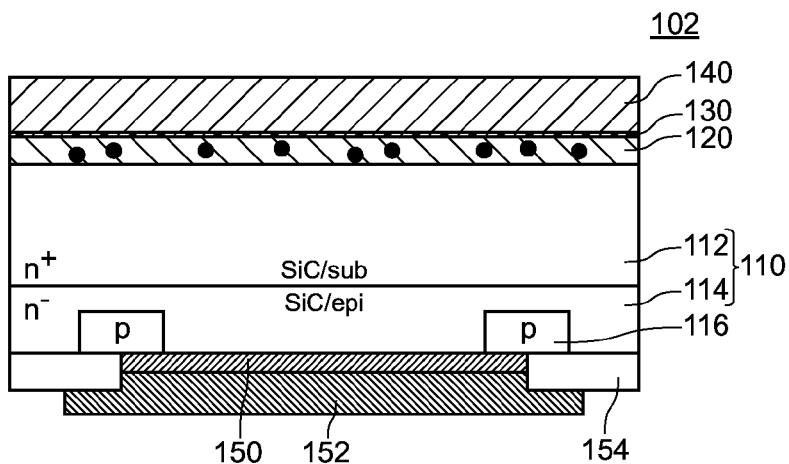


FIG. 5A

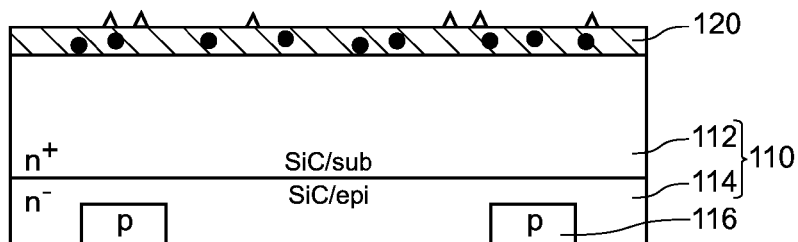


FIG. 5B

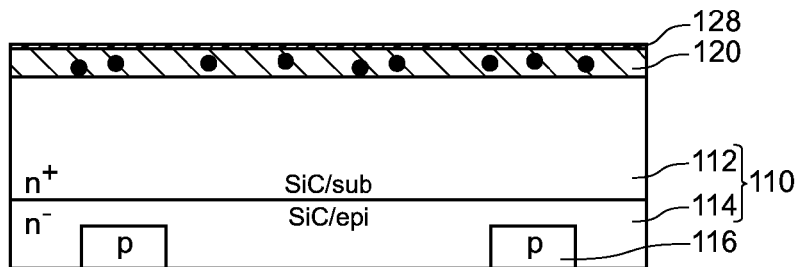


FIG. 5C

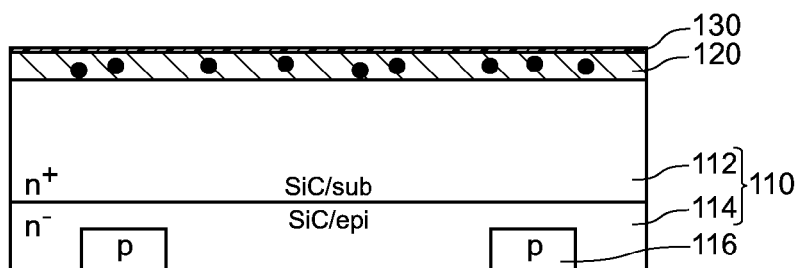


FIG. 5D

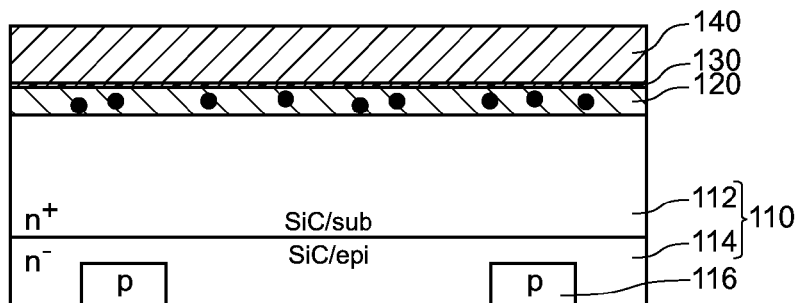


FIG. 5E

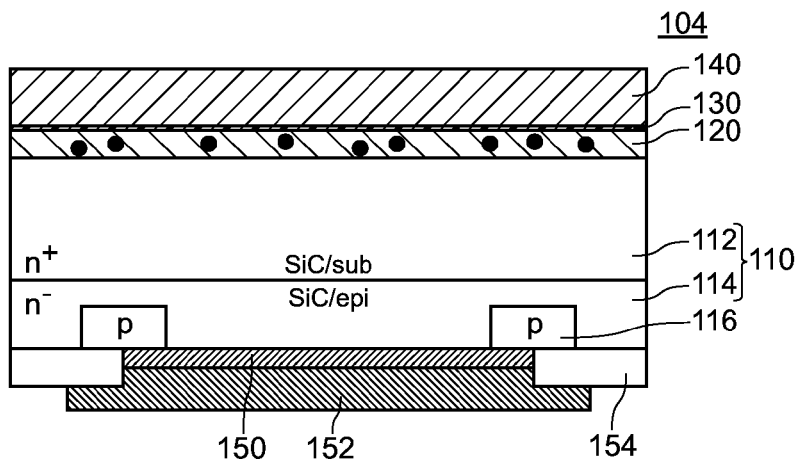


FIG. 6A

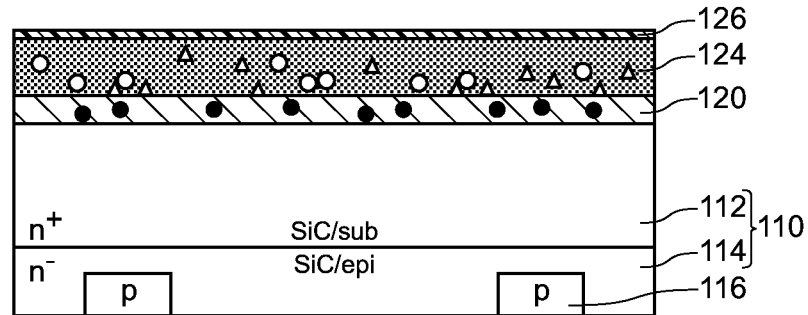


FIG. 6B

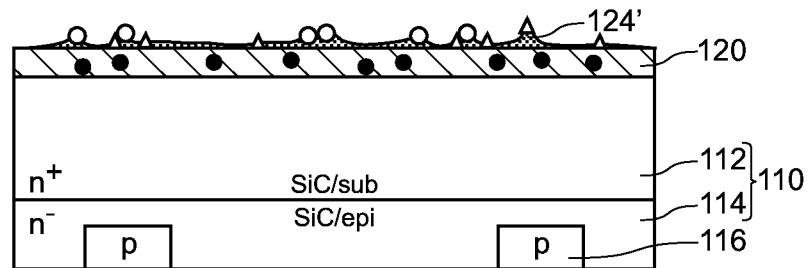


FIG. 6C

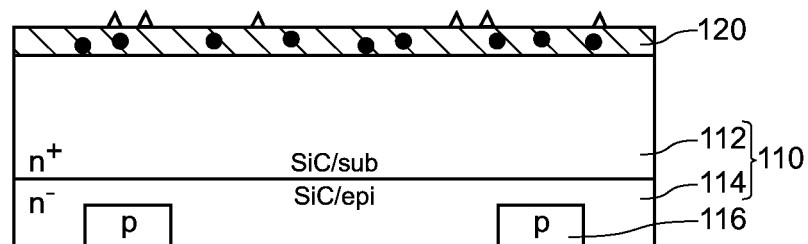
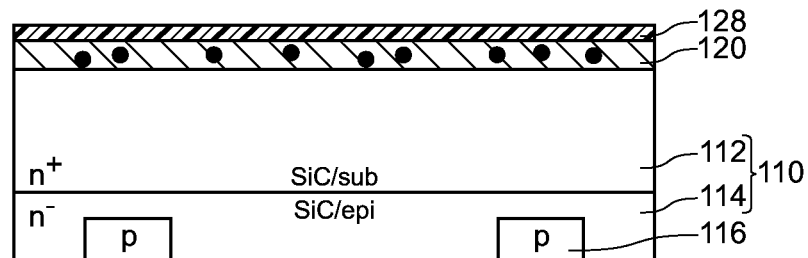


FIG. 6D





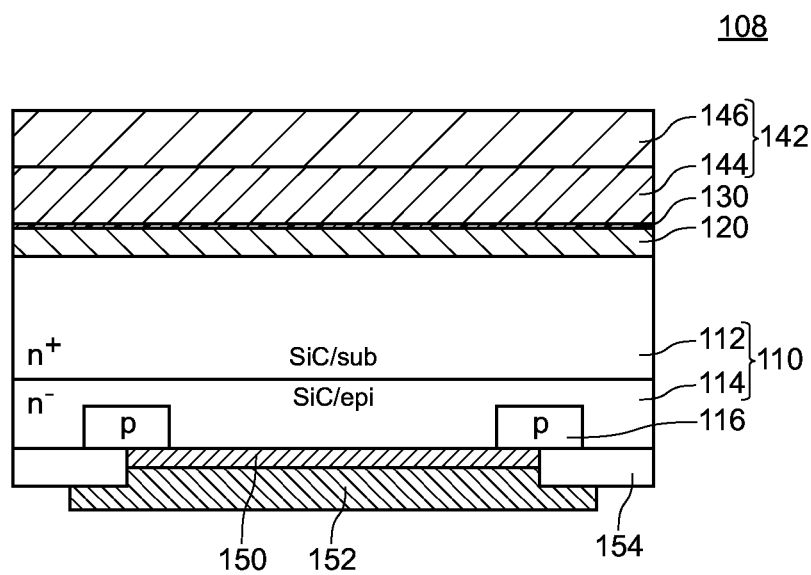


FIG.7

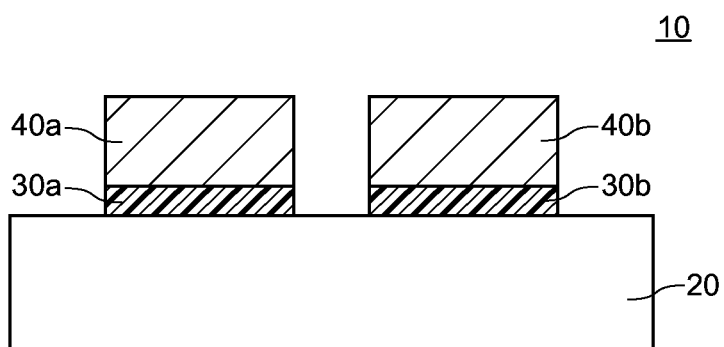


FIG.8

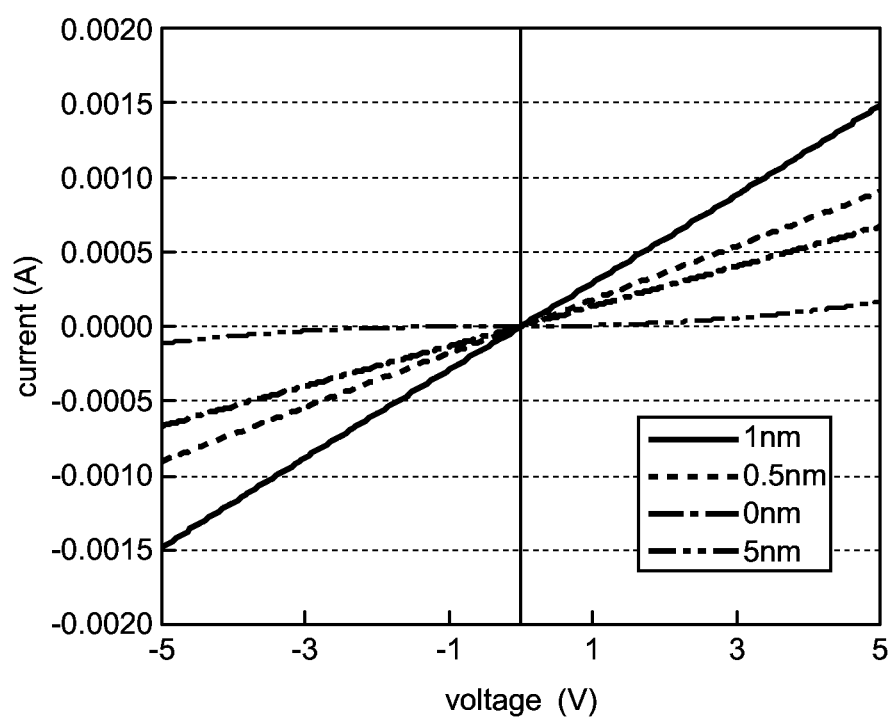


FIG.9

FIG.10A

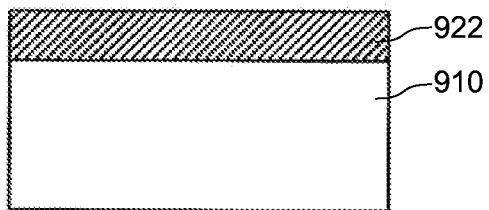


FIG.10B

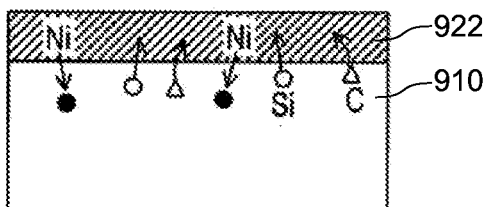


FIG.10C

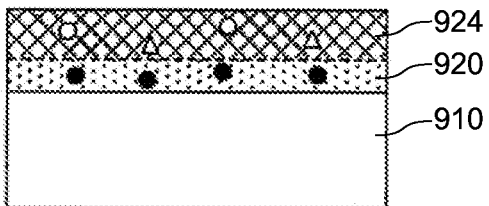


FIG.10D

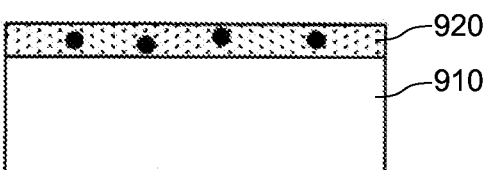
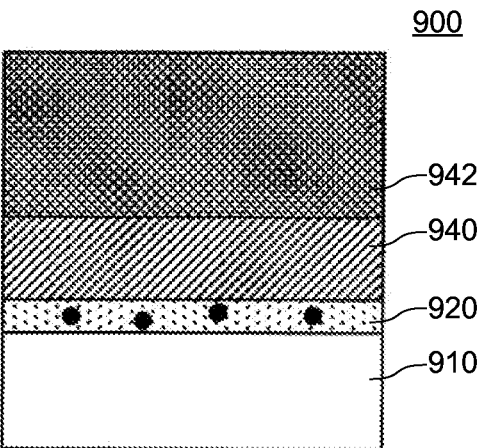


FIG.10E



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# SILICON CARBIDE SEMICONDUCTOR DEVICE AND METHOD FOR MANUFACTURING THE SAME

## RELATED APPLICATIONS

The present application is a National Phase of PCT/JP2011/070591, filed Sep. 9, 2011, and is based on, and claims priority from, Japanese Application No. 2011-086984, filed Apr. 11, 2011.

## TECHNICAL FIELD

The present invention relates to a silicon carbide semiconductor device and a method for manufacturing the silicon carbide semiconductor device.

## BACKGROUND ART

A silicon carbide semiconductor device is a semiconductor device which includes a silicon carbide layer, and has excellent technical features such as a high breakdown voltage, low loss, a low leakage current, high-temperature operability, and high-speed operability. Accordingly, the application of the silicon carbide semiconductor device to a power element such as a switching element or a rectifying element has been highly anticipated. As the power element, although a power MOSFET, an IGBT, a Schottky diode, a pn diode, a thyristor or the like has been known, all these power elements have an ohmic electrode which is in contact with a silicon carbide layer so that, in many cases, an electric current of several amperes flows between the silicon carbide layer and the ohmic electrode.

Conventionally, as a method for manufacturing a silicon carbide semiconductor device, there has been known a method described in patent literature 1 (a conventional method for manufacturing a silicon carbide semiconductor device). FIG. 10 is a view for explaining the conventional method for manufacturing a silicon carbide semiconductor device. FIG. 10(a) to FIG. 10(e) are views showing respective steps.

The conventional method for manufacturing a silicon carbide semiconductor device sequentially includes, as shown in FIG. 10, a conductive layer forming step where a conductive layer 922 made of nickel is formed on a silicon carbide layer 910 (see FIG. 10(a)), a heat treatment step where the silicon carbide layer 910 and the conductive layer 922 are made to react with each other thus forming an alloy layer formed of a reaction layer 920 which is in contact with the silicon carbide layer 910 and a silicide layer 924 present on the reaction layer 920 (see FIG. 10(b) and FIG. 10(c)), an etching step where at least a portion of the silicide layer 924 is removed using an acid thus exposing at least a portion of a surface of the reaction layer 920 (see FIG. 10(d)), and an electrode layer forming step where one electrode layer 940 and the other electrode layers 942 are formed on the exposed surface of the reaction layer 920 (see FIG. 10(e)) in this order.

According to the conventional method for manufacturing a silicon carbide semiconductor device, the alloy layer formed of the reaction layer 920 and the silicide layer 924 is formed on the surface of the silicon carbide layer 910 and, thereafter, the surface of the reaction layer 920 is exposed, and the electrode layer 940 and another electrode layer 942 are formed on the exposed surface of the reaction layer 920. Accordingly, not only the electrode layer 940 and the silicon carbide layer 910 are favorably bonded to each other with the reaction layer 920 interposed therebetween but also it is pos-

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sible to eliminate a possibility that a carbon component in the silicon carbide layer 910 diffuses into the electrode layer 940. As a result, the concentration of carbon in the surface of the electrode layer 940 can be lowered and hence, the adhesiveness between the electrode layer 940 and the other electrode layer 942 formed on the electrode layer 940 can be improved. Accordingly, it is possible to provide a highly reliable silicon carbide semiconductor device 900 where a possibility that the delamination of an electrode can be suppressed while ensuring a favorable contact between the silicon carbide layer and the electrode layer.

## PRIOR ART LITERATURE

### Patent Literature

Patent Literature 1: JP-A-2006-24880

## SUMMARY OF THE INVENTION

### Technical Problem

In the technical field to which semiconductor devices pertain, including a silicon carbide semiconductor device, there has been a demand for the further reduction of contact resistance between a semiconductor base body and an electrode layer.

In view of the above, the present invention has been made to overcome the above-mentioned drawbacks, and it is an object of the present invention to provide a silicon carbide semiconductor device which can realize the further reduction of contact resistance between a semiconductor base body and an electrode layer, and a method for manufacturing the silicon carbide semiconductor device.

### Solution to Problem

According to studies made by the inventors of the present invention, the inventors of the present invention have found that, by forming an electrode layer over a reaction layer with a predetermined conductive oxidation layer interposed therebetween instead of directly forming the electrode layer on the reaction layer, contact resistance between the semiconductor base body and the electrode layer can be further reduced. The present invention has been completed based on such finding. That is, the present invention is constituted of the following technical features.

[1] According to one aspect of the present invention, there is provided a silicon carbide semiconductor device which includes: a silicon carbide layer; a reaction layer and a conductive oxidation layer which is in contact with the reaction layer, the reaction layer and the conductive oxidation layer being formed by executing the steps in the following order: a conductive layer forming step where a conductive layer is formed on the silicon carbide layer; a heat treatment step where the silicon carbide layer and the conductive layer are made to react with each other thus forming the reaction layer which is in contact with the silicon carbide layer and a silicide layer which is present on the reaction layer; a first plasma ashing step where a carbon component which the silicide layer contains is removed; an etching step where at least a portion of the silicide layer is removed using an acid thus exposing at least a portion of a surface of the reaction layer; and a second plasma ashing step where a carbon component which remains on the reaction layer is removed and a conductive oxidation layer is formed on the reaction layer, and an

electrode layer which is formed over the reaction layer with the conductive oxidation layer interposed therebetween.

[2] In the silicon carbide semiconductor device of the present invention, it is preferable that a thickness of the conductive oxidation layer falls within a range of 0.3 nm to 2.25 nm.

[3] In the silicon carbide semiconductor device of the present invention, it is preferable that the acids are a hydrochloric acid, a nitric acid and a hydrofluoric acid.

[4] According to another aspect of the present invention, there is provided a method for manufacturing a silicon carbide semiconductor device for manufacturing the silicon carbide semiconductor device of the present invention which includes the steps in the following order: a conductive layer forming step where a conductive layer is formed on the silicon carbide layer; a heat treatment step where the silicon carbide layer and the conductive layer are made to react with each other thus forming a reaction layer which is in contact with the silicon carbide layer and a silicide layer which is present on the reaction layer; a first plasma ashing step where a carbon component which the silicide layer contains is removed; an etching step where at least a portion of the silicide layer is removed using an acid thus exposing at least a portion of a surface of the reaction layer; a second plasma ashing step where a carbon component which remains on the reaction layer is removed and a conductive oxidation layer which is in contact with the reaction layer is formed on the reaction layer; and an electrode layer forming step where an electrode layer is formed over the exposed reaction layer with the conductive oxidation layer interposed therebetween.

[5] In the method for manufacturing a silicon carbide semiconductor device of the present invention, it is preferable that a thickness of the conductive oxidation layer falls within a range of 0.3 nm to 2.25 nm.

[6] In the method for manufacturing a silicon carbide semiconductor device of the present invention, it is preferable that an oxidation layer which includes the conductive oxidation layer is formed on the reaction layer in the second plasma ashing step, and the method further comprises a second etching step where the oxidation layer formed in the second plasma ashing step is made thin so as to expose the conductive oxidation layer between the second plasma ashing step and the electrode layer forming step.

[7] In the method for manufacturing a silicon carbide semiconductor device of the present invention, it is preferable that an oxidation layer which includes the conductive oxidation layer is formed on the reaction layer in the second plasma ashing step, and the method further comprises a cleaning step where the oxidation layer formed in the second plasma ashing step is made thin so as to expose the conductive oxidation layer between the second plasma ashing step and the electrode layer forming step.

[8] In the method for manufacturing a silicon carbide semiconductor device of the present invention, it is preferable that an oxidation layer which is constituted of only the conductive oxidation layer is formed over the reaction layer in the second plasma ashing step.

[9] In the method for manufacturing a silicon carbide semiconductor device of the present invention, it is preferable that the second plasma ashing step is carried out using any one of an oxygen gas and a mixed gas of an oxygen gas and a hydrogen gas.

[10] In the method for manufacturing a silicon carbide semiconductor device of the present invention, it is preferable that the etching step is carried out using a hydrochloric acid, a nitric acid and a hydrofluoric acid.

[11] In the method for manufacturing a silicon carbide semiconductor device of the present invention, it is preferable that the etching step is carried out using an etchant which contains a hydrochloric acid, a nitric acid and a hydrofluoric acid.

[12] In the method for manufacturing a silicon carbide semiconductor device of the present invention, it is preferable that a content ratio among the hydrochloric acid, the nitric acid and the hydrofluoric acid which the etchant contains is set such that, assuming the content of the nitric acid as 100 mol, the content of the hydrochloric acid falls within a range of 300 mol to 500 mol, and the content of the hydrofluoric acid falls within a range of 0.1 mol to 5 mol.

[13] In the method for manufacturing a silicon carbide semiconductor device of the present invention, it is preferable that the etching step includes an etching step where an etchant A containing a hydrochloric acid is used and an etching step where an etchant B containing a nitric acid and a hydrofluoric acid is used.

[14] In the method for manufacturing a silicon carbide semiconductor device of the present invention, it is preferable that the content ratio between the nitric acid and the hydrofluoric acid which the etchant B contains is set such that, assuming the content of the nitric acid as 100 mol, the content of the hydrofluoric acid falls within a range of 0.1 mol to 5 mol.

[15] In the method for manufacturing a silicon carbide semiconductor device of the present invention, it is preferable that the first plasma ashing step is carried out using any one of an oxygen gas, a hydrogen gas and a mixed gas of an oxygen gas and a hydrogen gas.

#### Advantageous effects of Invention

According to the silicon carbide semiconductor device of the present invention, by forming an electrode layer over the reaction layer with the predetermined conductive oxidation layer interposed therebetween instead of forming the electrode layer directly on the reaction layer, contact resistance between the semiconductor base body (silicon carbide layer) and the electrode layer can be further reduced as can be understood from examples described later.

#### BRIEF DESCRIPTION OF DRAWINGS

##### FIG. 1

A cross-sectional view of a silicon carbide semiconductor device **100** according to an embodiment 1.

##### FIG. 2

A view for explaining a method for manufacturing a silicon carbide semiconductor device according to the embodiment 1.

##### FIG. 3

A view for explaining the method for manufacturing a silicon carbide semiconductor device according to the embodiment 1.

##### FIG. 4

A view for explaining a method for manufacturing a silicon carbide semiconductor device according to an embodiment 2.

##### FIG. 5

A view for explaining a method for manufacturing a silicon carbide semiconductor device according to an embodiment 3.

##### FIG. 6

A view for explaining a method for manufacturing a silicon carbide semiconductor device according to an embodiment 4.

##### FIG. 7

A cross-sectional view of a silicon carbide semiconductor device **108** according to an embodiment 5.

FIG. 8

A view for explaining an evaluation system **10** in examples. FIG. 9

A graph showing a result of evaluation in the examples.

FIG. 10

A view for explaining a conventional method for manufacturing a silicon carbide semiconductor device.

## DESCRIPTION OF EMBODIMENTS

Hereinafter, a silicon carbide semiconductor device and a method for manufacturing the silicon carbide semiconductor device of the present invention are explained in conjunction with embodiments shown in the drawings.

### Embodiment 1

FIG. 1 is a cross-sectional view of a silicon carbide semiconductor device **100** according to an embodiment 1.

As shown in FIG. 1, the silicon carbide semiconductor device **100** is a Schottky diode which includes: a silicon carbide layer **110**; a reaction layer **120**, a conductive oxidation layer **130** formed adjacent to the reaction layer **120** and a cathode electrode layer **140** (an electrode layer of the present invention) formed adjacent to the conductive oxidation layer **130**, all of which are formed on a first main surface side of the silicon carbide layer **100**; and a barrier metal layer **150**, an anode electrode layer **152** and a protective insulation layer **154** which are formed on a second main surface side of the silicon carbide layer **100**.

The silicon carbide layer **110** includes an  $n^+$  type silicon carbide substrate **112** and an  $n^-$  type epitaxial layer **114** containing  $n$ -type impurities at a concentration lower than a concentration of  $n$ -type impurities contained in the  $n^+$  type silicon carbide substrate **112**. A thickness of the  $n^+$  type silicon carbide substrate **112** is  $300\ \mu\text{m}$ , for example, and the concentration of  $n$ -type impurities in the  $n^+$  type silicon carbide substrate **112** is  $1 \times 10^{19}\ \text{cm}^{-3}$ , for example. A thickness of the  $n^-$  type epitaxial layer **114** is  $10\ \mu\text{m}$ , for example, and the concentration of  $n$ -type impurities in the  $n^-$  type epitaxial layer **114** is  $1 \times 10^{16}\ \text{cm}^{-3}$ , for example.

A  $p$ -type guard ring **116** is formed on a surface of the  $n^-$  type epitaxial layer **114** on a second main surface side. A concentration of  $p$ -type impurities in the guard ring **116** falls within a range of  $1 \times 10^{18}\ \text{cm}^{-3}$  to  $1 \times 10^{19}\ \text{cm}^{-3}$ , for example.

The reaction layer **120** is a layer which is formed by the diffusion of a nickel component into the  $n^+$  type silicon carbide substrate **112**. A concentration of nickel in the reaction layer **120** falls within a range of  $1.0 \times 10^3\ \text{cm}^{-3}$  to  $1.0 \times 10^4\ \text{cm}^{-3}$ , for example, and the concentration of nickel is gradually lowered along with the increase of a distance from a bonding surface between the reaction layer **120** and the conductive oxidation layer **130**. A thickness of the reaction layer **120** falls within a range of  $10\ \text{nm}$  to  $200\ \text{nm}$ , for example.

The conductive oxidation layer **130** is a conductive oxidation layer which is formed on the reaction layer **120** in a contact manner with the reaction layer **120**, and is formed by carrying out a second plasma ashing step for removing a carbon component which may remain on the reaction layer **120**. A thickness of the conductive oxidation layer **130** falls within a range of  $0.3\ \text{nm}$  to  $2.25\ \text{nm}$ , for example.

The cathode electrode layer **140** is formed by depositing metal (nickel, for example) which is a cathode electrode forming material over the reaction layer **120** by vapor depo-

sition with the conductive oxidation layer **130** interposed therebetween. A thickness of the cathode electrode layer **140** is  $2\ \mu\text{m}$ , for example.

The barrier metal layer **150** is made of metal (nickel, titanium or the like, for example) which forms a Schottky junction with the silicon carbide layer **110** ( $n^-$  type epitaxial layer **114**). A thickness of the barrier metal layer **150** is  $2\ \mu\text{m}$ , for example. The anode electrode layer **152** is formed on a surface of the barrier metal layer **150**. A thickness of the anode electrode layer **152** is  $5\ \mu\text{m}$ , for example. The anode electrode layer **152** is made of aluminum, for example. The protective insulation layer **154** is formed such that the protective insulation layer **154** surrounds the barrier metal layer **150** and the anode electrode layer **152**.

The silicon carbide semiconductor device **100** having the above-mentioned constitution can be manufactured by the following method (the method for manufacturing the silicon carbide semiconductor device according to the embodiment 1). Hereinafter, the method for manufacturing the silicon carbide semiconductor device according to the embodiment 1 is explained in accordance with manufacturing steps.

FIG. 2 and FIG. 3 are views for explaining the method for manufacturing a silicon carbide semiconductor device according to the embodiment 1. FIG. 2(a) to FIG. 2(e) and FIG. 3(a) to FIG. 3(e) are views showing respective steps.

#### 1. Silicon Carbide Layer Preparing Step

Firstly, the silicon carbide layer **110** having the structure where the  $n^+$  type silicon carbide substrate **112** and the  $n^-$  type epitaxial layer **114** are laminated to each other is prepared (see FIG. 2(a)). The  $p$ -type guard ring **116** is formed on the surface of the  $n^-$  type epitaxial layer **114**.

#### 2. Conductive Layer Forming Step

Next, a conductive layer **122** made of nickel is formed on a surface of the silicon carbide layer **110** ( $n^+$  type silicon carbide substrate **112**) on a first main surface side by EB vapor deposition, for example (see FIG. 2(b)). A thickness of the conductive layer **122** is set to  $50\ \text{nm}$  to  $500\ \text{nm}$ , for example. As a material for forming the conductive layer **122**, a metal material (aluminum, titanium, cobalt or the like) other than nickel may be used.

#### 3. Heat Treatment Step

Next, heat treatment is performed such that the silicon carbide layer **110** ( $n^+$  type silicon carbide substrate **112**) and the conductive layer **122** are made to react with each other thus forming an alloy layer formed of the reaction layer **120** which is in contact with the silicon carbide layer **110** ( $n^+$  type silicon carbide substrate **112**) and a silicide layer **124** which is present on the reaction layer **120**. Heat treatment is performed at a temperature of  $1000^\circ\text{C}$ . for 2 minutes in an inert atmosphere of highly purified argon (Ar) or the like from which moisture and oxygen are removed.

Due to such processing, the nickel component contained in the conductive layer **122** diffuses into the  $n^+$  type silicon carbide substrate **112** thus forming the reaction layer **120**, and a silicon component and a carbon component contained in the  $n^+$  type silicon carbide substrate **112** diffuse into the conductive layer **122** thus forming the silicide layer **124** (see FIG. 2(c) and FIG. 2(d)).

#### 4. First Plasma Ashing Step

Next, the carbon component contained in the silicide layer **124** is removed by first plasma ashing (see FIG. 2(e)). The first plasma ashing is carried out using an oxygen gas (ashing condition: output power  $1000\ \text{W}$ , ashing time  $5\ \text{min}$ ). By carrying out the first plasma ashing step, the carbon component in the vicinity of a surface of the silicide layer **124** is removed and hence, an etching step described later can be efficiently carried out. In this step, by carrying out the first

plasma ashing step, a nickel oxide layer **126** is formed on the surface of the silicide layer **124**.

#### 5. Etching Step

Next, a surface of the reaction layer **120** is exposed by removing the silicide layer **124** using an etchant containing a hydrochloric acid, a nitric acid and a hydrofluoric acid (etchant) (see FIG. 3(a)).

In the etching step, the nickel component is removed from the silicide layer **124** by a hydrochloric acid, and the silicon component is removed from the silicide layer **124** by a nitric acid and a hydrofluoric acid. Also in the etching step, the nickel oxide layer **126** which is formed in the first plasma ashing step is also removed. The content ratio among the hydrochloric acid, the nitric acid and the hydrofluoric acid which the etchant contains is set such that, assuming the content of the nitric acid as 100 mol, the content of the hydrochloric acid falls within a range of 300 mol to 500 mol, and the content of the hydrofluoric acid falls within a range of 0.1 mol to 5 mol.

#### 6. Second Plasma Ashing Step

Next, the carbon component on the surface of the reaction layer **120** is removed by second plasma ashing. The second plasma ashing is carried out using an oxygen gas. By carrying out the second plasma ashing, the carbon component can be removed from the surface of the reaction layer **120**. The second plasma ashing step is carried out under an ashing condition (output power 500 W, ashing time 5 min) where a thickness of an oxidation layer **128** becomes 10 nm, for example. In the second plasma ashing step, the oxidation layer **128** including "a conductive oxidation layer which is in contact with the reaction layer **120**" is formed on the reaction layer **120** (see FIG. 3(b)).

#### 7. Second Etching Step

Next, the oxidation layer **128** which is formed by the second plasma ashing step is made thin using an etchant containing a hydrofluoric acid thus exposing a conductive oxidation layer **130** (see FIG. 3(c)). The second etching step is carried out under a condition where a thickness of the conductive oxidation layer **130** falls within a range of 0.3 nm to 2.25 nm.

#### 8. Cathode Electrode Layer Forming Step

Next, the cathode electrode layer **140** made of nickel is formed over the reaction layer **120** with the conductive oxidation layer **130** interposed therebetween (on a surface of the conductive oxidation layer **130**) by physical vapor deposition (PVD) such as sputtering, for example (see FIG. 3(d)).

Next, the protective insulation layer **154**, the barrier metal layer **150** and the anode electrode layer **152** are formed on the surface of the n<sup>-</sup> type epitaxial layer **114** (see FIG. 3(e)).

By sequentially carrying out the above-mentioned steps, the silicon carbide semiconductor device **100** can be manufactured.

According to the silicon carbide semiconductor device and the method for manufacturing the silicon carbide semiconductor device of the embodiment 1, the electrode layer is formed over the reaction layer with the predetermined conductive oxidation layer interposed therebetween instead of forming the electrode layer directly on the reaction layer. Accordingly, contact resistance between the semiconductor base body (silicon carbide layer) and the electrode layer can be further reduced as can be understood from examples described later.

Further, according to the silicon carbide semiconductor device and the method for manufacturing the silicon carbide semiconductor device of the embodiment 1, the thickness of the conductive oxidation layer falls within a range of 0.3 nm to 2.25 nm. Accordingly, contact resistance between the semi-

conductor base body (silicon carbide layer) and the electrode layer can be further reduced as can be understood from examples described later.

However, according to studies that the inventors of the present invention have made, it is understood that, in the conventional method for manufacturing a silicon carbide semiconductor device, a nickel component in the silicide layer is selectively etched in the above-mentioned etching step so that a silicon component tends to remain on the reaction layer thus giving rise to a drawback that dispersion in device characteristics occurs.

There has been known a method for manufacturing a silicon carbide semiconductor device including a step where a silicide layer is removed by a CMP process in place of an etching process (another conventional method for manufacturing a silicon carbide semiconductor device, see JP-A-2009-10096, for example). According to this conventional method for manufacturing a silicon carbide semiconductor device, the silicide layer is removed by the CMP process and hence, there is no possibility that a silicon component remains on a reaction layer whereby it is possible to overcome a drawback that dispersion in device characteristics occurs. However, in this conventional method for manufacturing a silicon carbide semiconductor device, the silicide layer is removed by the CMP process and hence, there exists a drawback that productivity of the silicon carbide semiconductor devices is low.

To the contrary, according to the method for manufacturing a silicon carbide semiconductor device of the embodiment 1, the etching step is carried out using a hydrochloric acid, a nitric acid and a hydrofluoric acid and hence, both components, that is, a nickel component and a silicon component can be removed by the etching step. Accordingly, it is possible to overcome a drawback that dispersion in device characteristics occurs due to a silicon component remaining after an etching step.

Further, according to the method for manufacturing a silicon carbide semiconductor device of the embodiment 1, the silicide layer is removed by an etching process instead of a CMP process and hence, silicon carbide semiconductor devices can be manufactured with higher productivity than other conventional methods for manufacturing a silicon carbide semiconductor device.

Accordingly, the method for manufacturing a silicon carbide semiconductor device according to the embodiment 1 can overcome a drawback that dispersion in device characteristics occurs due to a silicon component remaining after an etching step, and also can manufacture silicon carbide semiconductor devices with high productivity.

#### Embodiment 2

FIG. 4 is a view for explaining a method for manufacturing a silicon carbide semiconductor device according to an embodiment 2. FIG. 4(a) to FIG. 4(e) are views showing respective steps. The method for manufacturing a silicon carbide semiconductor device according to the embodiment 2 includes the steps which exactly correspond to the steps of the method for manufacturing a silicon carbide semiconductor device according to the embodiment 1 shown in FIG. 2(a) to FIG. 2(e) respectively. Accordingly, the illustration of the steps of the method for manufacturing a silicon carbide semiconductor device according to the embodiment 2 corresponding to the steps shown in FIG. 2(a) to FIG. 2(e) is omitted.

Although the method for manufacturing a silicon carbide semiconductor device according to the embodiment 2 basically includes the substantially same steps as the method for

manufacturing a silicon carbide semiconductor device **100** according to the embodiment 1, the method for manufacturing a silicon carbide semiconductor device according to the embodiment 2 differs from the method for manufacturing a silicon carbide semiconductor device according to the embodiment 1 with respect to the details of the second plasma ashing step. That is, in the method for manufacturing a silicon carbide semiconductor device according to the embodiment 2, the second plasma ashing step is carried out under an ashing condition (output power 200 W, ashing time 3 min) which is weaker than the ashing condition used in the method for manufacturing a silicon carbide semiconductor device according to the embodiment 1. Further, by adopting such a second plasma ashing step, the second etching step is omitted. After the second plasma ashing step is carried out, the silicon carbide semiconductor device is cleaned using a cleaning liquid containing a diluted hydrofluoric acid and, then, the electrode forming step is carried out.

That is, in the method for manufacturing a silicon carbide semiconductor device according to the embodiment 2, as shown in FIG. 4(b) and FIG. 4(c), the oxidation layer **128** formed in the second plasma ashing step is made thin by carrying out the cleaning step so that the conductive oxidation layer **130** is exposed thus forming a surface. The cleaning step is carried out under a condition where a thickness of the conductive oxidation layer **128** after cleaning falls within a range of 0.3 nm to 2.25 nm.

In this manner, the method for manufacturing a silicon carbide semiconductor device according to the embodiment 2 differs from the method for manufacturing a silicon carbide semiconductor device according to the embodiment 1 with respect to the details of the second plasma ashing step. However, in the method for manufacturing a silicon carbide semiconductor device according to the embodiment 2, in the same manner as the silicon carbide semiconductor device and the method for manufacturing the silicon carbide semiconductor device according to the embodiment 1, the electrode layer is formed over the reaction layer with the predetermined conductive oxidation layer interposed therebetween instead of forming the electrode layer directly on the reaction layer and hence, contact resistance between the semiconductor base body (silicon carbide layer) and the electrode layer can be further reduced in the same manner as the silicon carbide semiconductor device and the method for manufacturing the silicon carbide semiconductor device according to the embodiment 1.

Further, according to the method for manufacturing a silicon carbide semiconductor device of the embodiment 2, in the same manner as the method for manufacturing the silicon carbide semiconductor device according to the embodiment 1, the etching step is carried out using a hydrochloric acid, a nitric acid and a hydrofluoric acid and hence, both components, that is, a nickel component and a silicon component can be removed by the etching step. Accordingly, it is possible to eliminate a possibility that dispersion in device characteristics occurs due to a silicon component remaining after an etching step.

Further, according to the method for manufacturing a silicon carbide semiconductor device of the embodiment 2, the silicide layer is removed by an etching process instead of a CMP process and hence, silicon carbide semiconductor devices can be manufactured with higher productivity than other conventional methods for manufacturing a silicon carbide semiconductor device.

Accordingly, the method for manufacturing a silicon carbide semiconductor device according to the embodiment 2, in the same manner as the method for manufacturing the silicon

carbide semiconductor device according to the embodiment 1, can overcome a drawback that dispersion in device characteristics occurs due to a silicon component remaining after an etching step, and also can manufacture silicon carbide semiconductor devices with high productivity.

### Embodiment 3

FIG. 5 is a view for explaining a method for manufacturing a silicon carbide semiconductor device according to an embodiment 3. FIG. 5(a) to FIG. 5(e) are views showing respective steps. The method for manufacturing a silicon carbide semiconductor device according to the embodiment 3 includes the steps which exactly correspond to the steps of the method for manufacturing a silicon carbide semiconductor device according to the embodiment 1 shown in FIG. 2(a) to FIG. 2(e) respectively. Accordingly, the illustration of the steps of the method for manufacturing a silicon carbide semiconductor device according to the embodiment 3 corresponding to the steps shown in FIG. 2(a) to FIG. 2(e) is omitted.

Although the method for manufacturing a silicon carbide semiconductor device according to the embodiment 3 basically includes the substantially same steps as the method for manufacturing a silicon carbide semiconductor device **100** according to the embodiment 1, the method for manufacturing a silicon carbide semiconductor device according to the embodiment 3 differs from the method for manufacturing a silicon carbide semiconductor device according to the embodiment 1 with respect to the details of the second plasma ashing step. That is, in the method for manufacturing a silicon carbide semiconductor device according to the embodiment 3, the second plasma ashing step is carried out under an ashing condition (output power 50 W, ashing time 1 min) which is further weaker than the ashing condition used in the method for manufacturing a silicon carbide semiconductor device according to the embodiment 2. Further, by adopting such a second plasma ashing step, the second etching step is omitted. After the second plasma ashing step is carried out, the silicon carbide semiconductor device is cleaned using a cleaning liquid not containing a hydrofluoric acid and, then, the electrode forming step is carried out.

That is, in the method for manufacturing a silicon carbide semiconductor device according to the embodiment 3, as shown in FIG. 5(b) and FIG. 5(c), the oxidation layer **128** which is constituted of only the conductive oxidation layer **130** is formed by carrying out the second plasma ashing step. The second plasma ashing step is carried out under a condition where a thickness of the oxidation layer **128** (that is, the conductive oxidation layer **130**) after the second plasma ashing step is carried out falls within a range of 0.3 nm to 2.25 nm.

In this manner, the method for manufacturing a silicon carbide semiconductor device according to the embodiment 3 differs from the method for manufacturing a silicon carbide semiconductor device according to the embodiment 1 with respect to the details of the second plasma ashing step. However, in the method for manufacturing a silicon carbide semiconductor device according to the embodiment 3, in the same manner as the silicon carbide semiconductor device and the method for manufacturing the silicon carbide semiconductor device according to the embodiment 1, the electrode layer is formed over the reaction layer with the predetermined conductive oxidation layer interposed therebetween instead of forming the electrode layer directly on the reaction layer and hence, contact resistance between the semiconductor base body (silicon carbide layer) and the electrode layer can be further reduced in the same manner as the silicon carbide



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semiconductor device and the method for manufacturing the silicon carbide semiconductor device according to the embodiment 1.

Further, according to the method for manufacturing a silicon carbide semiconductor device of the embodiment 3, in the same manner as the method for manufacturing the silicon carbide semiconductor device according to the embodiment 1, the etching step is carried out using a hydrochloric acid, a nitric acid and a hydrofluoric acid and hence, both components, that is, a nickel component and a silicon component can be removed by the etching step. Accordingly, it is possible to eliminate a possibility that dispersion in device characteristics occurs due to a silicon component remaining after an etching step.

Further, according to the method for manufacturing a silicon carbide semiconductor device of the embodiment 3, the silicide layer is removed by an etching process instead of a CMP process and hence, silicon carbide semiconductor devices can be manufactured with higher productivity than other conventional methods for manufacturing a silicon carbide semiconductor device.

Accordingly, the method for manufacturing a silicon carbide semiconductor device according to the embodiment 3, in the same manner as the method for manufacturing the silicon carbide semiconductor device according to the embodiment 1, can overcome a drawback that dispersion in device characteristics occurs due to a silicon component remaining after an etching step, and also can manufacture silicon carbide semiconductor devices with high productivity.

## Embodiment 4

FIG. 6 is a view for explaining a method for manufacturing a silicon carbide semiconductor device according to an embodiment 4. FIG. 6(a) to FIG. 6(d) are views showing respective steps. The method for manufacturing a silicon carbide semiconductor device according to the embodiment 4 includes the substantially same steps as the method for manufacturing a silicon carbide semiconductor device according to the embodiment 1 except for steps corresponding to the steps of the method for manufacturing a silicon carbide semiconductor device according to the embodiment 1 which are shown in FIG. 2(e), FIG. 3(a) and FIG. 3(b) respectively. Accordingly, the illustration of the steps of the method for manufacturing a silicon carbide semiconductor device according to the embodiment 4 corresponding to the steps shown in FIG. 2(a) to FIG. 2(d) and FIG. 3(c) to FIG. 3(e) is omitted.

Although the method for manufacturing a silicon carbide semiconductor device according to the embodiment 4 basically includes the substantially same steps as the method for manufacturing a silicon carbide semiconductor device according to the embodiment 1, the method for manufacturing a silicon carbide semiconductor device according to the embodiment 4 differs from the method for manufacturing a silicon carbide semiconductor device according to the embodiment 1 with respect to the details of the etching step. That is, in the method for manufacturing a silicon carbide semiconductor device according to the embodiment 4, an etching step where an etchant A containing a hydrochloric acid is used and an etching step where an etchant B containing a nitric acid and a hydrofluoric acid is used are carried out in this order.

In the first etching step, using the etchant A containing a hydrochloric acid, a nickel component in a nickel oxide layer

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126 which is formed by a first plasma ashing step and a nickel component in a silicide layer 124 are removed (see FIG. 6(a) and FIG. 6(b)).

In the second etching step, a silicon component in the silicide layer 124 is removed using the etchant B containing a nitric acid and a hydrofluoric acid (see FIG. 6(b) and FIG. 6(c)). As the etchant B, an etchant is used where the content ratio between the nitric acid and the hydrofluoric acid is set such that, assuming the content of the nitric acid as 100 mol, the content of the hydrofluoric acid falls within a range of 0.1 mol to 5 mol.

By carrying out the first etching step and the second etching step described above, at least a portion of a surface of a reaction layer 120 is exposed.

Thereafter, by sequentially carrying out a second plasma ashing step (see FIG. 6(d)), a second etching step and an electrode layer forming step (see FIG. 3(c) and FIG. 3(d)), a silicon carbide semiconductor device 108 according to the embodiment 4 can be manufactured.

In this manner, although the silicon carbide semiconductor device and the method for manufacturing the silicon carbide semiconductor device according to the embodiment 4 differs from the silicon carbide semiconductor device and the method for manufacturing the silicon carbide semiconductor device according to the embodiment 1 with respect to the details of the etching step, in the same manner as the silicon carbide semiconductor device and the method for manufacturing a silicon carbide semiconductor device according to the embodiment 1, the electrode layer is formed over the reaction layer with the predetermined conductive oxidation layer interposed therebetween instead of forming the electrode layer directly on the reaction layer and hence, contact resistance between the semiconductor base body (silicon carbide layer) and the electrode layer can be further reduced in the same manner as the silicon carbide semiconductor device and the method for manufacturing the silicon carbide semiconductor device according to the embodiment 1.

Further, according to the method for manufacturing a silicon carbide semiconductor device of the embodiment 4, in the same manner as the method for manufacturing a silicon carbide semiconductor device according to the embodiment 1, the etching step is carried out using a hydrochloric acid, a nitric acid and a hydrofluoric acid and hence, both components, that is, a nickel component and a silicon component can be removed by the etching step. Accordingly, it is possible to eliminate a possibility that dispersion in device characteristics occurs due to a silicon component remaining after an etching step.

Further, according to the method for manufacturing a silicon carbide semiconductor device of the embodiment 4, the silicide layer is removed by an etching process instead of a CMP process and hence, silicon carbide semiconductor devices can be manufactured with higher productivity than other conventional methods for manufacturing a silicon carbide semiconductor device.

Accordingly, the method for manufacturing a silicon carbide semiconductor device according to the embodiment 4, in the same manner as the method for manufacturing the silicon carbide semiconductor device according to the embodiment 1, can overcome a drawback that dispersion in device characteristics occurs due to a silicon component remaining after an etching step, and also can manufacture silicon carbide semiconductor devices with high productivity.

The silicon carbide semiconductor device and the method for manufacturing the silicon carbide semiconductor device according to the embodiment 4 includes the substantially same constitution or steps as the silicon carbide semiconductor

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tor device and the method for manufacturing the silicon carbide semiconductor device according to the embodiment 1 except for the etching step. Accordingly, the silicon carbide semiconductor device and the method for manufacturing the silicon carbide semiconductor device according to the embodiment 4 can acquire advantageous effects exactly equal to the advantageous effects acquired by the substantially same constitution or steps used in common by the embodiments 1 and 4 out of the advantageous effects that the silicon carbide semiconductor device and the method for manufacturing the silicon carbide semiconductor device according to the embodiment 1 possesses.

#### Embodiment 5

FIG. 7 is a cross-sectional view of a silicon carbide semiconductor device **108** according to an embodiment 5.

Although the silicon carbide semiconductor device **108** according to the embodiment 5 has the substantially same constitution as the silicon carbide semiconductor device **100** according to the embodiment 1, the silicon carbide semiconductor device **108** according to the embodiment 5 differs from the silicon carbide semiconductor device **100** according to the embodiment 1 with respect to the constitution of a cathode electrode layer.

That is, as shown in FIG. 7, the silicon carbide semiconductor device **108** according to the embodiment 5 includes a cathode electrode layer **142** which is formed by laminating a first cathode electrode layer **144** and a second cathode electrode layer **146** to each other as the cathode electrode layer.

The first cathode electrode layer **144** is, in the same manner as the above-mentioned cathode electrode layer **140**, formed by depositing metal (for example, titanium) which is a first cathode electrode material over a reaction layer **120** by vapor deposition with a conductive oxidation layer **130** interposed therebetween. A thickness of the first cathode electrode layer **144** is set to 0.5  $\mu\text{m}$ , for example. The second cathode electrode layer **146** is formed by depositing metal (for example, nickel) which is a second cathode electrode material on the first cathode electrode layer **144** by vapor deposition. A thickness of the second cathode electrode layer **146** is set to 2  $\mu\text{m}$ , for example.

In this manner, the silicon carbide semiconductor device **108** according to the embodiment 5 differs from the silicon carbide semiconductor device **100** according to the embodiment 1 with respect to the constitution of the cathode electrode layer. However, in the silicon carbide semiconductor device **108** according to the embodiment 5, in the same manner as the silicon carbide semiconductor device according to the embodiment 1, the electrode layer is formed over the reaction layer with the predetermined conductive oxidation layer interposed therebetween instead of forming the electrode layer directly on the reaction layer and hence, contact resistance between the semiconductor base body (silicon carbide layer) and the electrode layer can be further reduced in the same manner as the silicon carbide semiconductor device according to the embodiment 1.

According to the silicon carbide semiconductor device **108** according to the embodiment 5, an alloy layer formed of the reaction layer **120** and the silicide layer **124** is formed on a surface of a silicon carbide layer **110** and, thereafter, a surface of the reaction layer **120** is exposed, and the first cathode electrode layer (one electrode layer) **144** and the second cathode electrode layer (the other electrode layer) **146** are formed over the exposed surface of the reaction layer **120** with the conductive oxidation layer **130** interposed therebetween. Accordingly, not only the first cathode electrode layer **144**

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and the silicon carbide layer **110** are favorably bonded to each other with the reaction layer **120** and the conductive oxidation layer **130** interposed therebetween but also it is possible to eliminate a possibility that a carbon component in the silicon carbide layer **110** diffuses into the first cathode electrode layer **144**. As a result, the concentration of carbon in the surface of the first cathode electrode layer **144** can be lowered and hence, the adhesiveness between the first cathode electrode layer **144** and the second cathode electrode layer **146** formed on the first cathode electrode layer **144** can be improved. Accordingly, there is also an advantage that it is possible to provide a highly reliable silicon carbide semiconductor device where a possibility that an electrode is peeled off is suppressed while ensuring a favorable contact between the silicon carbide layer and the electrode layer.

#### Example

This example is provided for proving that contact resistance between a semiconductor base body and an electrode layer can be further reduced when the electrode layer is formed over a reaction layer with a conductive oxidation layer interposed therebetween. FIG. 8 is a view for explaining an evaluation system **10** used in the example, and FIG. 9 is a graph showing a result of evaluation in the example.

##### 1. Specimens

The evaluation system **10** is, as shown in FIG. 8, prepared by forming conductive oxidation layers **30a**, **30b** on a surface of a silicon carbide layer (silicon carbide semiconductor base body) **20** using the same manner as the first embodiment 1, and by forming electrode layers **40a**, **40b** made of nickel on surfaces of the conductive oxidation layers **30a**, **30b**. The impurity concentration of the silicon carbide layer **20** is  $1 \times 10^{19} \text{ cm}^{-3}$ . An area of each electrode layer **40a**, **40b** is 5000  $\mu\text{m}^2$  (50  $\mu\text{m} \times 100 \mu\text{m}$ ). The respective electrode layers **40a**, **40b** are arranged such that longer sides (sides of 100  $\mu\text{m}$ ) of the respective electrode layers **40a**, **40b** face each other in an opposed manner. A distance between the electrode layer **40a** and the electrode layer **40b** is set to 3  $\mu\text{m}$ . The respective electrode layers **40a**, **40b** are formed over the silicon carbide layer **20** by vapor deposition with the conductive oxidation layers **30a**, **30b** interposed therebetween.

##### 2. Evaluation Method

A current-voltage characteristic when thicknesses of the conductive oxidation layers **30a**, **30b** of the evaluation system **10** are changed within a range of 0 nm to 5 nm and a voltage within a range of -5V to +5V is applied between the electrode layers **40a**, **40b**, is measured, and the evaluation of the specimens is performed. In this case, bulk resistance of the semiconductor base body **20** is not changed between the respective specimens and hence, a current value shown in FIG. 9 becomes large when the contact resistance between the semiconductor base body **20** and each electrode layer **40a**, **40b** becomes small. Accordingly, in the graph shown in FIG. 9, the greater the inclination in the rightward and upward direction, the smaller the contact resistance between the semiconductor base body **20** and each electrode layer **40a**, **40b** is.

##### 3. Result of Evaluation

As can be clearly understood from FIG. 9, it is found that in the case where the conductive oxidation layers **30a**, **30b** having a thickness of 0.5 nm or 1.0 nm are interposed between the semiconductor base body **20** and the respective electrode layers **40a**, **40b** respectively, the contact resistance between the semiconductor base body **20** and each electrode layer **40a**, **40b** becomes small compared to the case where conductive oxidation layers are not interposed between the semiconductor base body **20** and the respective electrode layers **40a**, **40b**.

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respectively. It is also found that in the case where the conductive oxidation layers **30a**, **30b** having a thickness of 5 nm are interposed between the semiconductor base body **20** and the respective electrode layers **40a**, **40b** respectively, the contact resistance between the semiconductor base body **20** and each electrode layer **40a**, **40b** becomes large compared to the case where conductive oxidation layers are not interposed between the semiconductor base body **20** and the respective electrode layers **40a**, **40b** respectively. As a result of the more detailed investigation, it is found that in the case where the conductive oxidation layers **30a**, **30b** having a thickness of 0.3 nm to 2.25 nm are interposed between the semiconductor base body **20** and the respective electrode layers **40a**, **40b** respectively, the contact resistance between the semiconductor base body **20** and each electrode layer **40a**, **40b** can be reduced compared to the case where conductive oxidation layers are not interposed between the semiconductor base body **20** and the respective electrode layers **40a**, **40b** respectively.

Although the present invention has been explained in conjunction with the above-mentioned embodiments heretofore, the present invention is not limited to the above-mentioned embodiments. The present invention can be carried out in various modifications without departing from the gist of the present invention. For example, the following modifications are conceivable.

(1) Although the etching step where an etchant A containing a hydrochloric acid is used and the etching step where an etchant B containing a nitric acid and a hydrofluoric acid is used are carried out in this order in the above-mentioned embodiment 2, the present invention is not limited to such an order. For example, the etching step where an etchant B containing a nitric acid and a hydrofluoric acid is used and the etching step where an etchant A containing a hydrochloric acid is used may be carried out in this order.

(2) The first plasma ashing step is carried out using an oxygen gas in the above-mentioned respective embodiments. However, the present invention is not limited to such embodiments. For example, the first plasma ashing step may be carried out using "a hydrogen gas" or "a mixed gas of an oxygen gas and a hydrogen gas" instead of using an oxygen gas.

(3) The second plasma ashing step is carried out using an oxygen gas in the above-mentioned respective embodiments. However, the present invention is not limited to such embodiments. For example, the second plasma ashing step may be carried out using "a mixed gas of an oxygen gas and a hydrogen gas" instead of using an oxygen gas.

(4) In the above-mentioned respective embodiments, the method for manufacturing a silicon carbide semiconductor device of the present invention has been explained by taking a Schottky diode as an example. However, the present invention is not limited to such embodiments. For example, the present invention is also applicable to a method for manufacturing a silicon carbide semiconductor device which includes a step where an electrode layer is formed over a silicon carbide layer with a reaction layer such as a power MOSFET, an IGBT, a pn diode or a thyristor interposed therebetween.

(5) In the above-mentioned respective embodiments, the present invention has been explained by taking the case where the n-type silicon carbide layer is used as an example. However, the present invention is not limited to such embodiments. The present invention is also applicable to a case where a p-type silicon carbide layer is used, for example.

## REFERENCE SIGNS LIST

**100**, **102**, **104**, **106**, **108**, **900**: silicon carbide semiconductor device, **110**, **910**: silicon carbide layer, **112**, **912**: n<sup>+</sup> type

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silicon carbide substrate, **114**: n<sup>-</sup> type epitaxial layer, **116**: guard ring, **120**, **920**: reaction layer, **122**, **922**: conductive layer, **124**, **924**: silicide layer, **126**: nickel oxide layer, **128**: oxidation layer, **130**: conductive oxidation layer, **140**, **142**: cathode electrode layer, **144**: first cathode electrode layer, **146**: second cathode electrode layer, **150**: barrier metal layer, **152**: anode electrode layer, **154**: protective insulation layer, **940**: electrode layer, **942**: other electrode layer

The invention claimed is:

**1.** A silicon carbide semiconductor device comprising:  
a silicon carbide layer;

a reaction layer and a conductive oxidation layer which is in contact with the reaction layer, the reaction layer and the conductive oxidation layer being formed by executing the steps in the following order: a conductive layer forming step where a conductive layer is formed on the silicon carbide layer; a heat treatment step where the silicon carbide layer and the conductive layer are made to react with each other thus forming the reaction layer which is in contact with the silicon carbide layer and a silicide layer which is present on the reaction layer; a first plasma ashing step where a carbon component which the silicide layer contains is removed; an etching step where at least a portion of the silicide layer is removed using an acid thus exposing at least a portion of a surface of the reaction layer; and a second plasma ashing step where a carbon component which remains on the reaction layer is removed and a conductive oxidation layer is formed on the reaction layer, and  
an electrode layer which is formed over the reaction layer with the conductive oxidation layer interposed therebetween.

**2.** The silicon carbide semiconductor device according to claim **1**, wherein a thickness of the conductive oxidation layer falls within a range of 0.3 nm to 2.25 nm.

**3.** The silicon carbide semiconductor device according to claim **1**, wherein the acids are a hydrochloric acid, a nitric acid and a hydrofluoric acid.

**4.** A method for manufacturing a silicon carbide semiconductor device for manufacturing the silicon carbide semiconductor device; the method comprising the steps in the following order:

a conductive layer forming step where the conductive layer is formed on a silicon carbide layer;

a heat treatment step where the silicon carbide layer and the conductive layer are made to react with each other thus forming a reaction layer which is in contact with the silicon carbide layer and a silicide layer which is present on the reaction layer;

a first plasma ashing step where a carbon component which the silicide layer contains is removed;

an etching step where at least a portion of the silicide layer is removed using an acid thus exposing at least a portion of a surface of the reaction layer;

a second plasma ashing step where a carbon component which remains on the reaction layer is removed and a conductive oxidation layer which is in contact with the reaction layer is formed on the reaction layer; and

an electrode layer forming step where an electrode layer is formed over the exposed reaction layer with the conductive oxidation layer interposed therebetween.

**5.** The method for manufacturing a silicon carbide semiconductor device according to claim **4**, wherein a thickness of the conductive oxidation layer falls within a range of 0.3 nm to 2.25 nm.

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6. The method for manufacturing a silicon carbide semiconductor device according to claim 4, wherein an oxidation layer which includes the conductive oxidation layer is formed on the reaction layer in the second plasma ashing step, and

the method further comprises a second etching step where the oxidation layer formed in the second plasma ashing step is made thin so as to expose the conductive oxidation layer between the second plasma ashing step and the electrode layer forming step.

7. The method for manufacturing a silicon carbide semiconductor device according to claim 4, wherein an oxidation layer which includes the conductive oxidation layer is formed on the reaction layer in the second plasma ashing step, and

the method further comprises a cleaning step where the oxidation layer formed in the second plasma ashing step is made thin so as to expose the conductive oxidation layer between the second plasma ashing step and the electrode layer forming step.

8. The method for manufacturing a silicon carbide semiconductor device according to claim 4, wherein an oxidation layer which is constituted of only the conductive oxidation layer is formed over the reaction layer in the second plasma ashing step.

9. The method for manufacturing a silicon carbide semiconductor device according to claim 4, wherein the second plasma ashing step is carried out using any one of an oxygen gas and a mixed gas of an oxygen gas and a hydrogen gas.

10. The method for manufacturing a silicon carbide semiconductor device according to claim 4, wherein the etching step is carried out using a hydrochloric acid, a nitric acid and a hydrofluoric acid.

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11. The method for manufacturing a silicon carbide semiconductor device according to claim 10, wherein the etching step is carried out using an etchant which contains a hydrochloric acid, a nitric acid and a hydrofluoric acid.

12. The method for manufacturing a silicon carbide semiconductor device according to claim 11, wherein a content ratio among the hydrochloric acid, the nitric acid and the hydrofluoric acid which the etchant contains is set such that, assuming the content of the nitric acid as 100 mol, the content of the hydrochloric acid falls within a range of 300 mol to 500 mol, and the content of the hydrofluoric acid falls within a range of 0.1 mol to 5 mol.

13. The method for manufacturing a silicon carbide semiconductor device according to claim 10, wherein the etching step includes an etching step where an etchant A containing a hydrochloric acid is used and an etching step where an etchant B containing a nitric acid and a hydrofluoric acid is used.

14. The method for manufacturing a silicon carbide semiconductor device according to claim 13, wherein the content ratio between the nitric acid and the hydrofluoric acid which the etchant B contains is set such that, assuming the content of the nitric acid as 100 mol, the content of the hydrofluoric acid falls within a range of 0.1 mol to 5 mol.

15. The method for manufacturing a silicon carbide semiconductor device according to claim 4, wherein the first plasma ashing step is carried out using any one of an oxygen gas, a hydrogen gas and a mixed gas of an oxygen gas and a hydrogen gas.

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